

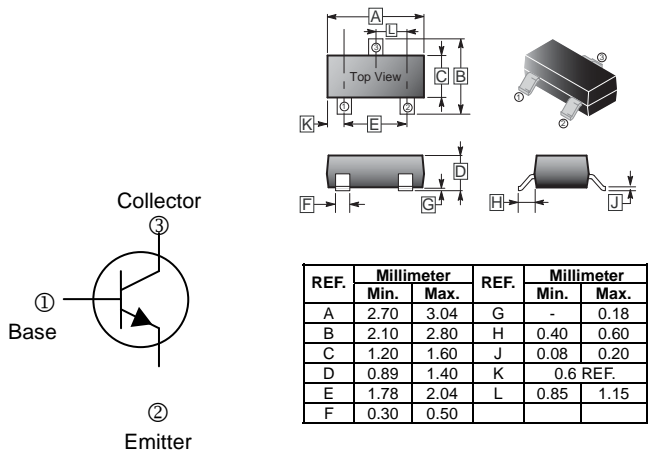
RoHS Compliant Product
A suffix of "-C" specifies halogen & lead-free

SOT-23

FEATURES

- Complimentary to SS8550
- Power Dissipation
 $P_{CM} : 0.3W$
- Collector Current
 $I_{CM} : 1.5A$
- Collector - Base Voltage
 $V_{(BR)CBO} : 40V$
- Operating & Storage junction temperature
 $T_J, T_{STG} : -55^{\circ}C \sim +150^{\circ}C$

MARKING : Y1



MAXIMUM RATINGS (at $T_a = 25^{\circ}C$ unless otherwise specified)

PARAMETER	SYMBOL	RATINGS	UNIT
Collector - Base Voltage	V_{CBO}	40	V
Collector - Emitter Voltage	V_{CEO}	25	V
Emitter - Base Voltage	V_{EBO}	5	V
Collector Current - Continuous	I_C	1.5	A
Collector Power Dissipation	P_C	0.3	W
Junction, Storage Temperature	T_J, T_{STG}	150, -55-150	$^{\circ}C$

ELECTRICAL CHARACTERISTICS (at $T_a = 25^{\circ}C$ unless otherwise specified)

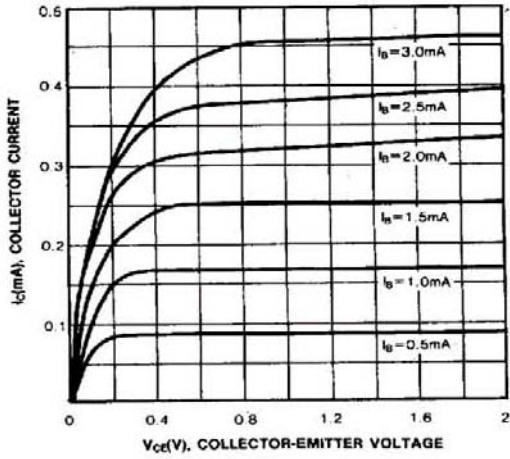
PARAMETER	TEST CONDITIONS	SYMBOL	MIN.	MAX.	UNIT
Collector-Base Breakdown Voltage	$I_C = 100\mu A, I_E = 0$	$V_{(BR)CBO}$	40		V
Collector-Emitter Breakdown Voltage	$I_C = 0.1mA, I_B = 0$	$V_{(BR)CEO}$	25		V
Emitter-Base Breakdown Voltage	$I_E = 100\mu A, I_C = 0$	$V_{(BR)EBO}$	5		V
Collector Cut-Off Current	$V_{CB} = 40V, I_E = 0$	I_{CBO}		0.1	μA
Collector Cut-Off Current	$V_{CB} = 20V, I_E = 0$	I_{CEO}		0.1	μA
Emitter Cut-Off Current	$V_{EB} = 5V, I_C = 0$	I_{EBO}		0.1	μA
DC Current Gain	$V_{CE} = 1V, I_C = 100mA$	h_{FE1}	120	400	
	$V_{CE} = 1V, I_C = 800mA$	h_{FE2}	40		
Collector-Emitter Saturation Voltage	$I_C = 800mA, I_B = 80mA$	$V_{CE(sat)}$		0.5	V
Base-Emitter Saturation Voltage	$I_C = 800mA, I_B = 80mA$	$V_{BE(sat)}$		1.2	V
Transition Frequency	$V_{CE} = 10V, I_C = 50mA, f = 30MHz$	F_T	100		MHz

CLASSIFICATION OF hFE

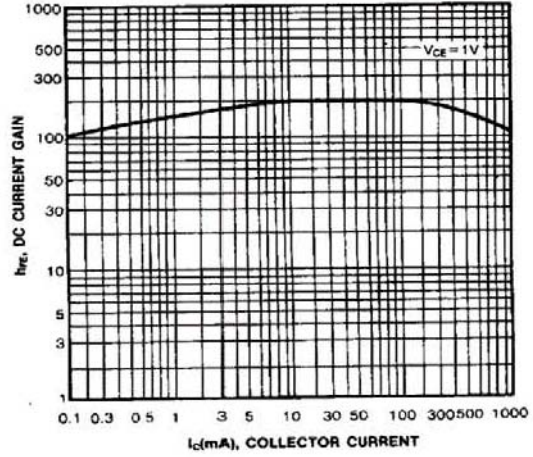
RANK	L	H	J
RANGE	120-200	200-350	300-400
MARKING	Y1		

CHARACTERISTIC CURVES

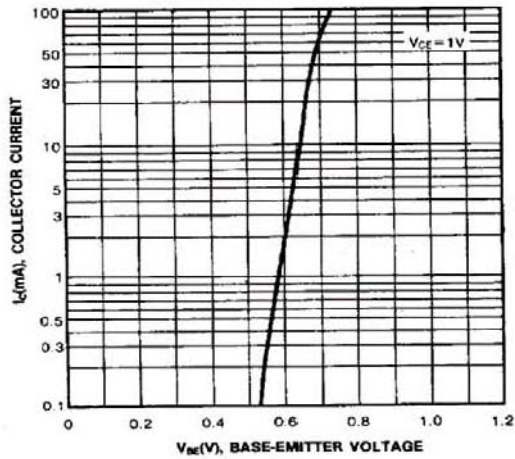
STATIC CHARACTERISTIC



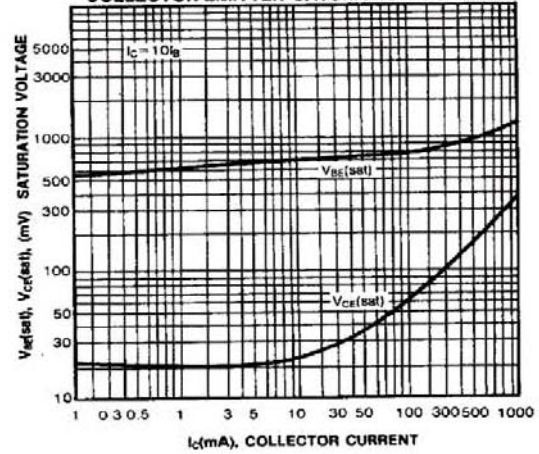
DC CURRENT GAIN



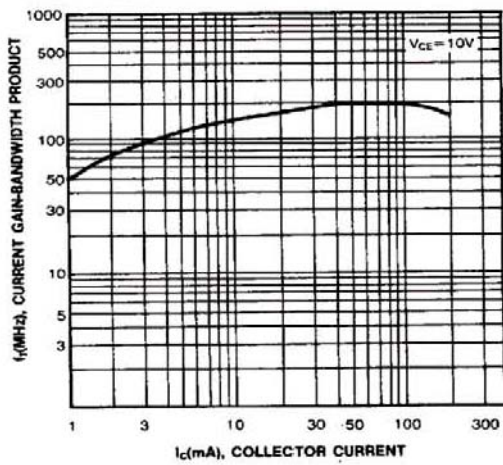
BASE-EMITTER ON VOLTAGE



**BASE-EMITTER SATURATION VOLTAGE
COLLECTOR-EMITTER SATURATION VOLTAGE**



CURRENT GAIN-BANDWIDTH PRODUCT



COLLECTOR OUTPUT CAPACITANCE

